L Number	Hits	Search Text	DB	Time stamp
-	28022	etchant or "etching gas"	USPAT;	2002/12/17 18:10
ļ			US-PGPUB	
-	145	(adsorb\$3 or adsorption or condens\$3 or condensation) with	USPAT;	2002/12/17 21:18
		(etchant or "etching gas")	US-PGPUB	000040473440
-	994349	water	USPAT;	2002/12/17 21:18
			US-PGPUB	2002/12/17 21:19
-	21966	ozone and water	USPAT; US-PGPUB	2002/12/17 21:18
	10405	(+	USPAT;	2002/12/17 21:19
[-	10405	(adsorb\$3 or adsorption or condens\$3 or condensation) and	US-PGPUB	2002/12/17 21.19
}	215	(ozone and water) (etchant or "etching gas") and ((adsorb\$3 or adsorption or	USPAT;	2002/12/17 21:19
-	215	condens\$3 or condensation) and (ozone and water))	US-PGPUB	2002/12/17 21/19
	553830	semiconductor or "integrated circuit" or silicon	USPAT;	2002/12/17 21:20
-	333630	Series in the state of sines in	US-PGPUB	2002/22/27
_	3533	((adsorb\$3 or adsorption or condens\$3 or condensation)	USPAT;	2002/12/17 21:21
	3333	and (ozone and water)) and (semiconductor or "integrated	US-PGPUB	
		circuit" or silicon)		
_	200	(adsorb\$3 or adsorption or condens\$3 or condensation) with	USPAT;	2002/12/17 21:21
		ozone with water	US-PGPUB	
-	15	(US-6337277-\$ or US-6099945-\$ or US-6024888-\$ or	USPAT;	2002/12/18 12:25
		US-5935454-\$ or US-5500079-\$ or US-5354416-\$ or	US-PGPUB	
		US-5087323-\$ or US-5030319-\$ or US-6299696-\$).did. or	İ	
}		(US-20020177323-\$ or US-20020121502-\$ or		
		US-20020038681-\$ or US-20010006849-\$ or		
		US-20020134409-\$ or US-20020122753-\$).did.		2002/42/40 42-26
-	490771	wafer or substrate	USPAT;	2002/12/18 12:26
	700450		US-PGPUB	2002/12/10 12:26
-	700153	cool\$3	USPAT; US-PGPUB	2002/12/18 12:26
	22000	(wafer or substrate) with cool\$3	USPAT;	2002/12/18 12:27
-	22000	(water of substrate) with cool\$3	US-PGPUB	2002/12/10 12.27
_	29628	ozone	USPAT;	2002/12/18 12:27
	23020	Ozone	US-PGPUB	2002, 22, 20 22,2,
_	828	((wafer or substrate) with cool\$3) and ozone	USPAT;	2002/12/18 12:27
			US-PGPUB	
-	347653	@ad>20000523 @rlad>20000523	USPAT;	2002/12/18 12:28
(US-PGPUB	
-	649	(((wafer or substrate) with cool\$3) and ozone) not	USPAT;	2002/12/18 12:28
		(@ad>20000523 @rlad>20000523)	US-PGPUB	
-	1021500	water or steam	USPAT;	2002/12/18 12:29
			US-PGPUB	
-	486	((((wafer or substrate) with cool\$3) and ozone) not	USPAT;	2002/12/18 12:29
	20222	(@ad>20000523 @rlad>20000523)) and (water or steam)	US-PGPUB	2002/12/10 12:20
-	392087	adsorb\$3 or adsorption or condens\$3 or condensation	USPAT; US-PGPUB	2002/12/18 12:30
	200	((((()wafer or cubstrate) with coold?) and exerc) not	USPAT;	2002/12/18 12:30
	289	((((((wafer or substrate) with cool\$3) and ozone) not (@ad>20000523 @rlad>20000523)) and (water or steam))	US-PGPUB	2002/12/10 12:30
		and (adsorb\$3 or adsorption or condens\$3 or condensation)	35 . 3. 05	
[_	52	(semiconductor or "integrated circuit" or silicon) and	USPAT;	2002/12/18 15:18
	32	((adsorb\$3 or adsorption or condens\$3 or condensation)	US-PGPUB	,,
		with ozone with water)		
-	288	((((((wafer or substrate) with cool\$3) and ozone) not	USPAT;	2002/12/18 12:31
		(@ad>20000523 @rlad>20000523)) and (water or steam))	US-PGPUB	
		and (adsorb\$3 or adsorption or condens\$3 or		
		condensation)) not ((semiconductor or "integrated circuit" or		
		silicon) and ((adsorb\$3 or adsorption or condens\$3 or		
		condensation) with ozone with water))		200244242 := :=
-	35	(semiconductor or "integrated circuit" or silicon) and	EPO; JPO;	2002/12/18 15:19
		((adsorb\$3 or adsorption or condens\$3 or condensation)	DERWENT;	1
	L	and ozone and water)	IBM_TDB	L

	12	(semiconductor or "integrated circuit" or silicon) and	EPO; JPO;	2002/12/18 15:22
-	12	((adsorb\$3 or adsorption or condens\$3 or condensation)	DERWENT;	2002/12/10 13.22
	1	((adsorbas or adsorption or condensas or condensation) with ozone with water)	IBM_TDB	!
	23	((semiconductor or "integrated circuit" or silicon) and	EPO; JPO;	2002/12/18 15:22
-	23	((adsorb\$3 or adsorption or condens\$3 or condensation)	DERWENT;	2002/12/10 15.22
	}	and ozone and water)) not ((semiconductor or "integrated	IBM_TDB	
		circuit" or silicon) and ((adsorb\$3 or adsorption or	מטו_ויוסג	
		condens\$3 or condensation) with ozone with water))	1	
	74	(US-6337277-\$ or US-6099945-\$ or US-6024888-\$ or	USPAT;	2002/12/18 17:38
-	71			2002/12/16 17.50
		US-5935454-\$ or US-5500079-\$ or US-5354416-\$ or	US-PGPUB;	
		US-5087323-\$ or US-5030319-\$ or US-6299696-\$ or	DERWENT	
	Į	US-6432845-\$ or US-6429493-\$ or US-6403498-\$ or		
		US-6368891-\$ or US-6358830-\$ or US-6350685-\$ or	}	
		US-6340435-\$ or US-6284205-\$ or US-6281141-\$ or		
		US-6246105-\$ or US-6245659-\$ or US-6239041-\$ or		
	1	US-6238511-\$ or US-6232156-\$ or US-6194304-\$ or		
		US-6184068-\$ or US-6144097-\$).did. or (US-6143081-\$ or		
		US-6107182-\$ or US-5967156-\$ or US-5962194-\$ or		\
		US-5953634-\$ or US-5925577-\$ or US-5923962-\$ or		
	Ì	US-5904770-\$ or US-5843833-\$ or US-5840600-\$ or		
		US-5714306-\$ or US-5643826-\$ or US-5078832-\$ or		
		US-4911103-\$ or US-4910043-\$ or US-4906328-\$ or		
		US-4891488-\$ or US-4886570-\$ or US-4877757-\$ or		
		US-4875989-\$ or US-4863558-\$ or US-4857132-\$ or		
		US-4855160-\$ or US-4844773-\$ or US-4842687-\$ or		
	Ì	US-4842676-\$ or US-4836905-\$).did. or (US-4832779-\$ or		
		US-4832777-\$ or US-4830705-\$ or US-4830700-\$ or		Í
•		US-4822450-\$ or US-4818327-\$ or US-4818326-\$ or		
		US-4778532-\$).did. or (US-20020177323-\$ or]	
		US-20020121502-\$ or US-20020038681-\$ or		
	İ	US-20010006849-\$ or US-20020134409-\$ or		
		US-20020122753-\$).did. or (JP-2001276758-\$ or	1	
		US-20020050279-\$ or US-20020020436-\$ or	1	
		WO-200137329-\$).did.		
-	1	("6240933").PN.	USPAT;	2002/12/18 17:38
			US-PGPUB	Ì